Application/Control Number: 10/615,038

Art Unit: 2800

Clmpto 07/26/05 PY

- 1. (original) A method for fabricating a capacitor, comprising the steps of:
- a) forming a lower electrode on a semiconductor substrate;
- b) forming a dielectric layer on the lower electrode;
- c) loading the semiconductor substrate containing the dielectric layer into a deposition chamber;
- d) nitriding a surface of the dielectric layer while NH₃ gas is flowed into the deposition chamber; and
- c) forming an upper layer by using a source gas NH₃, containing Titanium (Ti) on the nitrated surface of the dielectric layer through an atomic layer deposition (ALD) method.
- 2. (original) The method as recited in claim 1, wherein the step d) is performed on condition that the source gas NH₃ is flowed in at a flow rate of about 300 secm to about 1000 secm for about 10 seconds to about 120 seconds.
- 7. (currently amended) The method as recited in claim 3, wherein step b1) further includes the steps of:
 - a2) absorbing the TiCl4 onto the dielectric layer by feeding the TiCl4;
- b2) feeding the TiCl₄ gas in order to make it absorbed adsorb the TiCl₄ on onto the dielectric layer;
- c2) purging a remnant remnants of the TiCl4 gas remaining after the absorption;
- d2) feeding NH₃ gas on onto a surface of the dielectric layer on which the TiCl₄ is already obserbed adsorbed; and
- e2) purging a remnant of the NH₃ gas and a by-product which is formed by a chemical reaction between the NH₃ and the TiCl₄.
- 8. (new) The method as recited in claim 1, wherein the upper layer includes a TiN layer formed by the ALD method using TiCl₄ gas as a precursor.